

IN THE SPECIFICATION

Please replace the paragraph beginning at page 1, line 4, with the following replacement paragraph:

~~--The present application claims priority to Japanese Application No. P2000-083367 filed March 24, 2000, which application is incorporated herein by reference to the extent permitted by law.~~This application is a divisional of co-pending application Serial Number 09/816,055, filed March 23, 2001. The present and foregoing applications claim priority to Japanese Application No. P2000-083367, filed on March 24, 2000. All of the foregoing applications are incorporated herein by reference to the extent permitted by law.--

Please replace the Abstract of the Disclosure with the following replacement Abstract of the Disclosure:

--A semiconductor device of MCM type allowing high-density assembly and a process of fabricating the same is provided. There are provided semiconductor chips mounted on a supporting substrate and incrustrated in an insulation film on the supporting substrate and wiring formed in the insulation film so as to connect to each semiconductor chip through connection holes provided in the insulation film. Then, an interlayer dielectric covers such wiring that is connected to an upper layer wiring, through connection holes provided in such interlayer dielectric. In addition, an upper layer insulation film covers the upper layer wiring, and an electrode, connected to such upper layer wiring through another connection hole, is provided on such upper layer insulation film.

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~~— In addition, an upper layer insulation film covers the upper layer wiring, and an electrode, connected to such upper layer wiring through another connection hole, is provided on such upper layer insulation film.--~~